

Device Modeling Report

COMPONENTS: Light-Emitting Diode (LED) STANDARD
PART NUMBER: SLP-WB89A-51
MANUFACTURER: SANYO
REMARK: TA=60 degree C

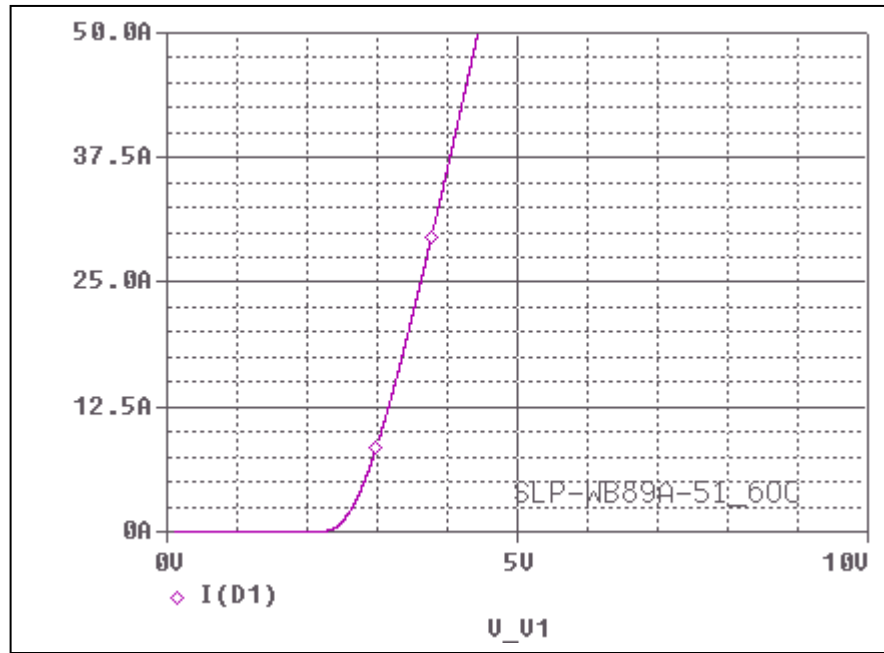


Bee Technologies Inc.

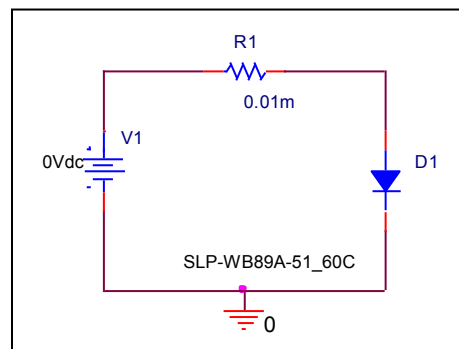
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

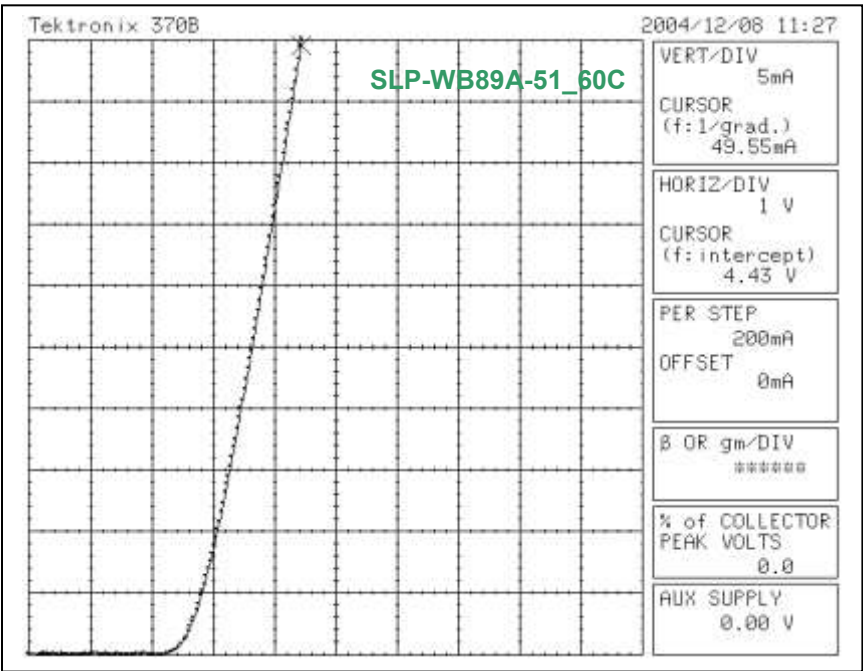


Evaluation Circuit



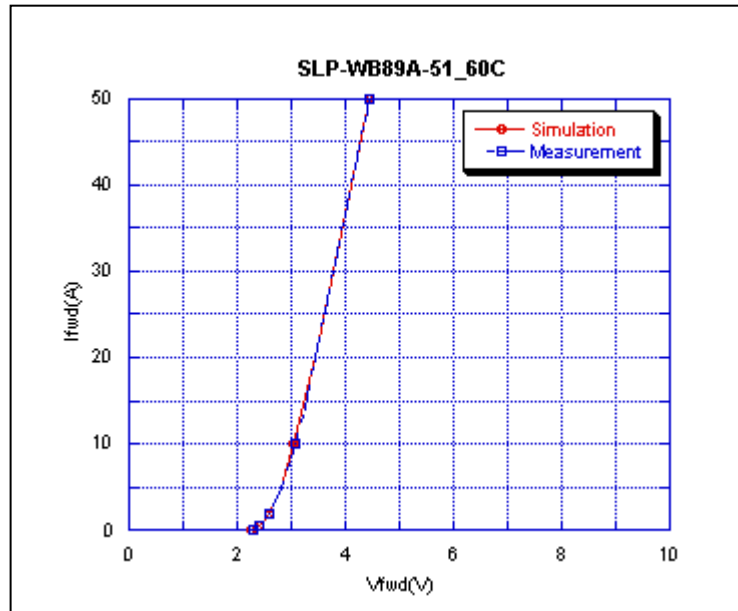
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

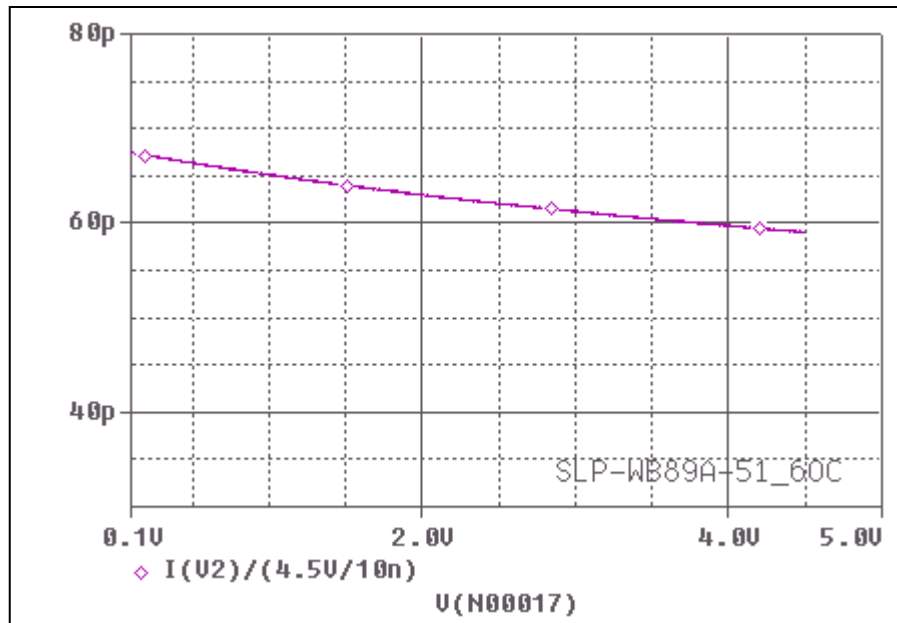


Simulation Result

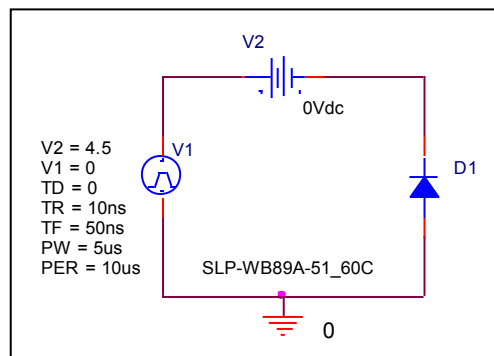
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.1	2.29	2.27	0.8733
0.2	2.33	2.33	0
0.5	2.41	2.417	0.2904
1	2.49	2.497	0.2811
2	2.6	2.604	0.1538
5	2.8	2.811	0.3928
10	3.07	3.055	0.4885
20	3.45	3.443	0.2028
50	4.43	4.437	0.1580

Capacitance Characteristic

Circuit Simulation Result

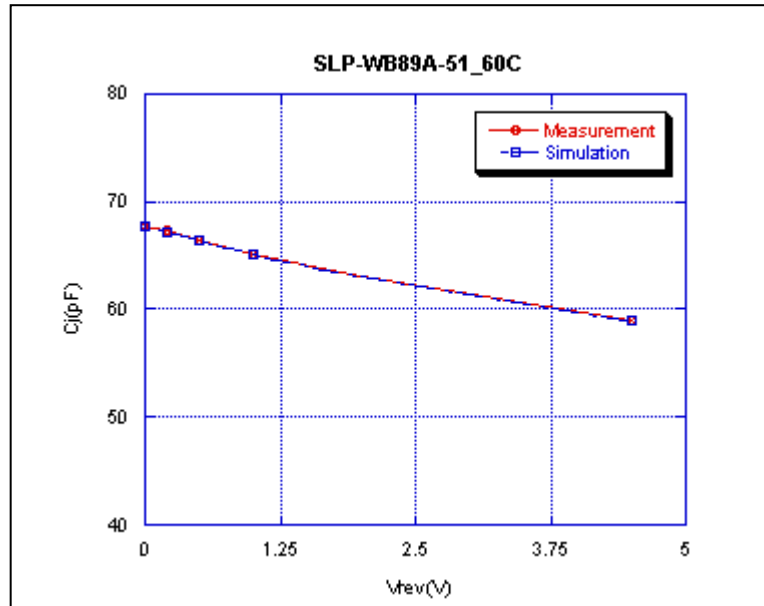


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

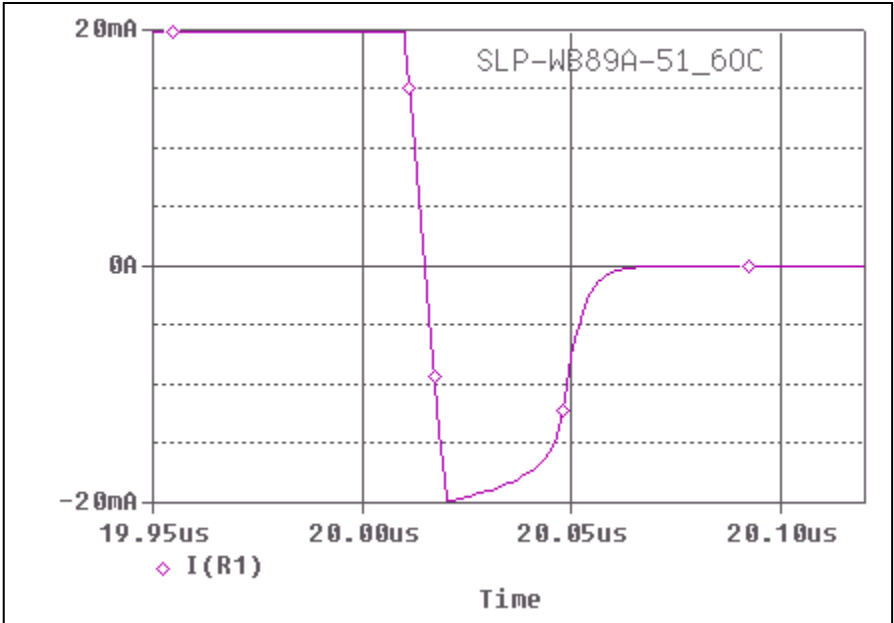


Simulation Result

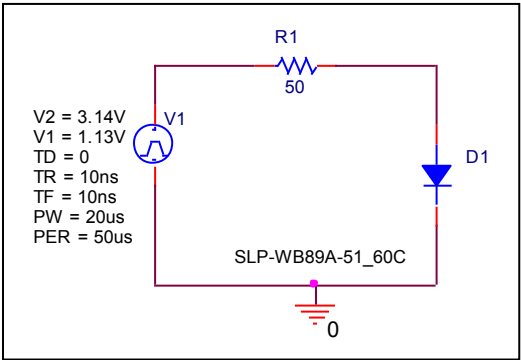
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	67.72	67.72	0
0.1	67.49	67.49	0
0.2	67.24	67.18	0.0892
0.5	66.36	66.34	0.0301
1	65.105	65.13	0.0383
2	63.02	63.05	0.0476
4.5	59.05	59.03	0.0338

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

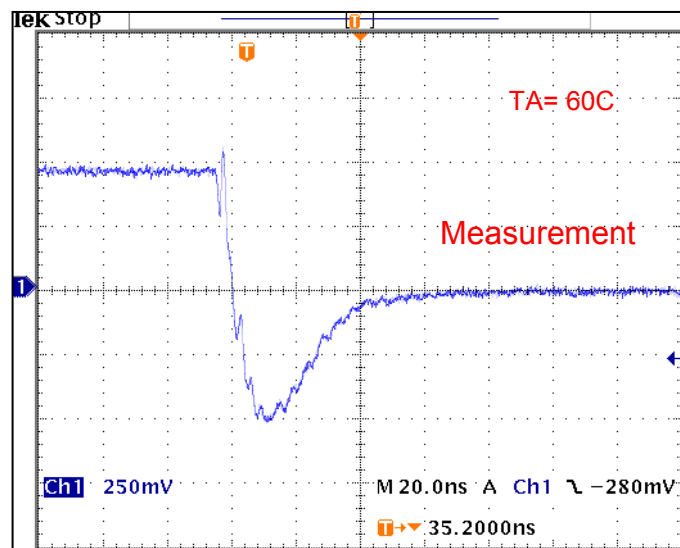


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
$T_{rr}=t_{rj}+t_{rb}$	39.2	ns	39.4	ns	0.510

Reverse Recovery Characteristic

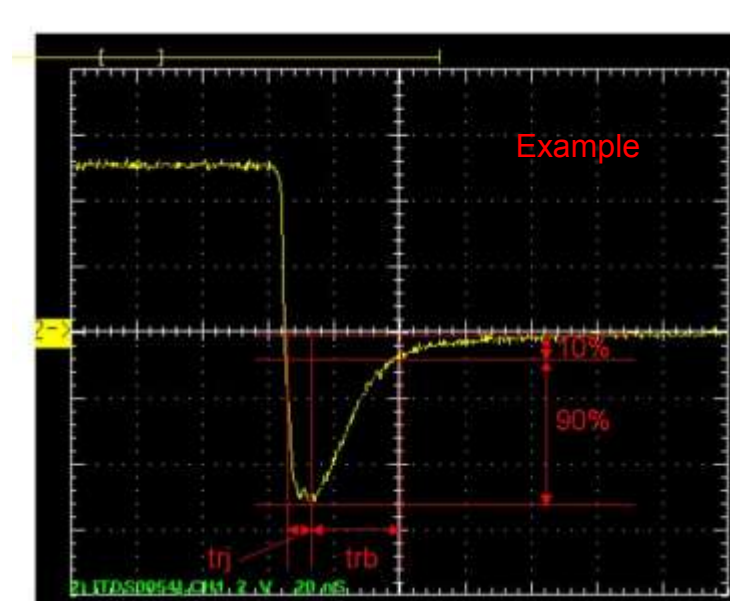
Reference



$Trj = 10(\text{ns})$

$Trb = 29.2(\text{ns})$

Conditions: $I_{fwd} = I_{rev} = 0.02(\text{A})$, $R_I = 50$



Relation between trj and trb